Plenary Talk

Overview on Low Power SoC Design Technology

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Outline

1. Background

Trend on power dissipation in SoC

- 2. Conventional design techniques to reduce leakage
- 3. Techniques to reduce Active Leakage
- 4. Summary

Trend on Power Dissipation



- Dynamic power increases as device gets scaled
- Leakage power increases exponentially becomes equal to dynamic power at 20nm @RT; at 50nm @100C

3

Design techniques to reduce subthreshold leakage



Power Gating



- Technique to turn off supply voltage using Power Switch (PS) to reduce leakage power
- Originally, used to reduce standby leakage

Approaches to reduce Active Leakage

- Power Gating to turn off PS even in operation time
 "Run-time Power Gating "
- Run-time Power Gating approaches
 - Module-level approach
 - Fine-grained approach



Module-level Run-time Power Gating

- Renesas Technology's mobile processor
- Partitioned into 20 Power Domains based on module
- Power Switch for each Power Domain controlled at run time corresponding to "scenes"





Courtesy: T. Hattori, et al, ISSCC2006, DAC'06

Module-level Run-time Power Gating (cont.)

Scene : Video telephony



Leakage: 849µA (RT, 1.2V)

Scene : Waiting for calling



Leakage: 299 μ A (RT, 1.2V)

Courtesy: T. Hattori, et al, ISSCC2006, DAC'06

Fine-grained Run-time Power Gating

• Typical structure for gated clock design



 When enable = 0, stored data in F/F is not updated output of combinational logic is logically "don't care"

• Exploiting enable signal of gated clock



K. Usami, et al, ICCD2006



 Partitioning logic gates into power-domains based on enable signals

K. Usami, et al, ICCD2006



- Logic gate and Power Switch are defined as "cell"
- V-GND line is routed as inter-cell wire

- Applied to datapath in embedded microprocessor
- Datapath was partitioned into 66 Power domains based on enable signals



Power Switch cells highlighted in purple

Total: 17085 cells incl. 1866 PS cells

- Active leakage power reduced by 83% at 90nm
- Area penalty by 20%

K. Usami, et al, ICCD2006

Summary

- Power dissipation in SoC gets more serious as device is scaled
- Share of leakage in the total operation power increases in further scaled devices
- Run-time Power Gating will become important to reduce active leakage power

Thank you !